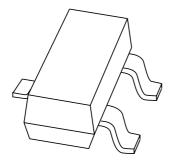
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBD353 Schottky barrier double diode

Product specification Supersedes data of 1999 May 25 2001 Oct 15





Schottky barrier double diode

PMBD353

FEATURES

- Low forward voltage
- Small SMD package
- · Low capacitance.

APPLICATIONS

- UHF mixer
- · Sampling circuits
- Modulators
- Phase detection.

DESCRIPTION

Planar Schottky barrier double diode in a SOT23 small plastic SMD package.

MARKING

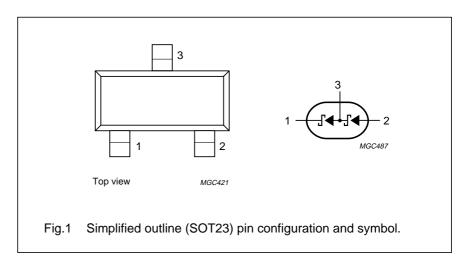
TYPE NUMBER	MARKING CODE ⁽¹⁾		
PMBD353	*4F		

Note

- 1. * = p: Made in Hong Kong.* = t: Made in Malaysia.
 - * = W: Made in China.

PINNING

PIN	DESCRIPTION				
1	cathode k ₁				
2	anode a ₂				
3	common connection a ₁ , k ₂				



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT		
Per diode						
V _R	continuous reverse voltage – 4 V					
I _F	continuous forward current – 30 mA					
T _{stg}	storage temperature	+150	°C			
Tj	junction temperature – 100 °C					

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V _F	forward voltage	see Fig.2		
		I _F = 0.1 mA	350	mV
		I _F = 1 mA	450	mV
		I _F = 10 mA	600	mV
I _R	reverse current	V _R = 3 V; note 1; see Fig.3	0.25	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.4	1	pF

Note

1. Pulse test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

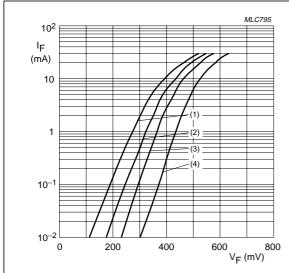
Note

1. Refer to SOT23 standard mounting conditions.

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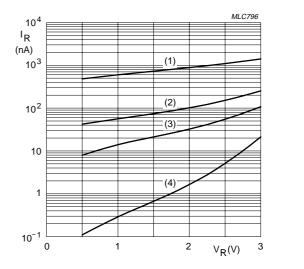
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GRAPHICAL DATA



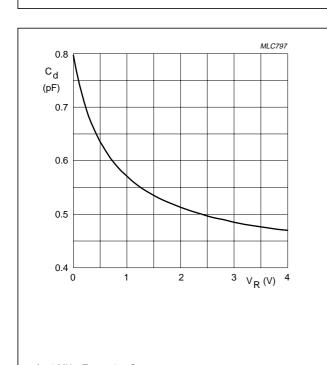
- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) $T_{amb} = 60 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.
- (4) $T_{amb} = -40 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) $T_{amb} = 60 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.
- (4) $T_{amb} = -40 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

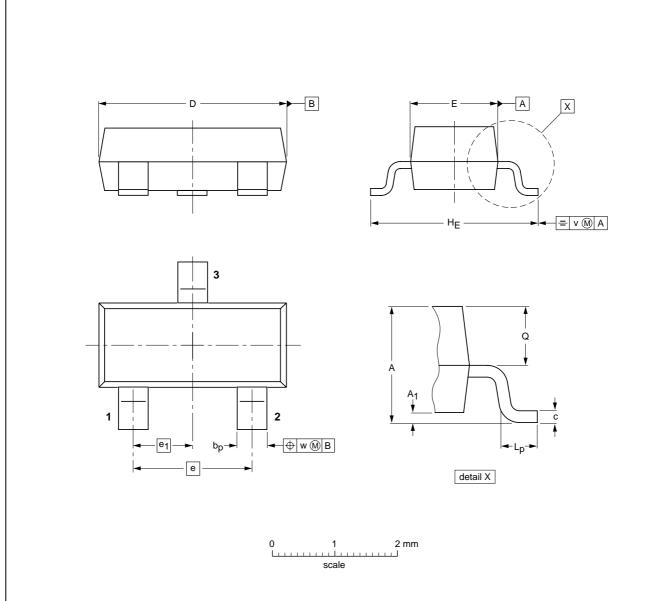
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS	(mm are	the original	dimensions)
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UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLIN	IE		REFER	EUROPEAN	ISSUE DATE		
VERSIO	N	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23	3		TO-236AB				97-02-28 99-09-13

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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NOTES

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